IN THE SPECIFICATION:

Please replace the paragraph at page 30, lns. 2-21 with the following amended paragraph:

Fig. 10B is a top view of almost one pixel. A sectional structure along the line B-B' in the drawing is shown in Fig. 11. In the sectional structure shown in Fig. 11, although a structural example using a single crystalline silicon substrate is shown, such a structure can be realized in the same way even if an SOI substrate is used. An n-well region 302 and a p-well region 303 are formed in a substrate 301, and a field oxide film 304 is formed to separate adjacent FETs. The switching FET 330 is formed of a p-channel FET, and includes a gate insulating film 305, a gate electrode 307, a side wall 309, an LDD region 311, a source region 312, a drain region 313, a source wiring 318, and a drain wiring 319. The current controlling transistor 331 is an n-channel FET, and includes a gate insulating film 306, a gate electrode 308, a side wall 310, an LDD region 314, a source region 315, a drain region 316, a source wiring 320, and a drain wiring 321. An interlayer insulating film 317 is formed thereon. A passivation film 334 is formed on the switching FET 330 and the current controlling transistor 331. The storage capacitance 332 is formed on an interlayer insulating film 322, and is formed of a capacitance electrode 323 connected to the drain wiring 319 of the switching FET 330, a power supply line 19a, and a dielectric layer 324 provided therebetween. Here, when the capacitance electrode 323 is formed of a material containing an element selected from Al, Ta and Ti as its main ingredient, and the dielectric layer 324 is formed by anodic oxidation of its surface, an excellent storage capacitance can be formed. The organic EL component 333 is formed through an interlayer insulating film 326, and is formed of an EL component lower electrode 327 connected to the drain wiring 321 of the current controlling FET 331, an organic EL layer 328, and an EL

component upper electrode 329.